

MRT250.16

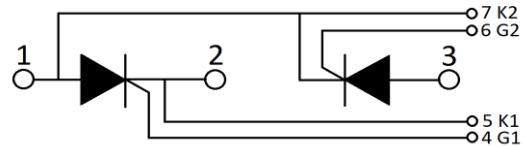
Thyristors module

Features:

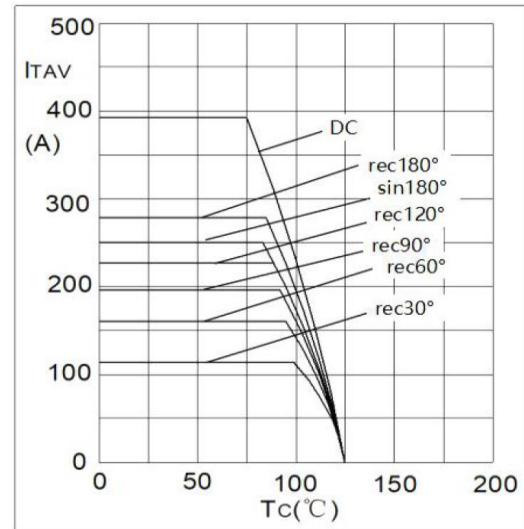
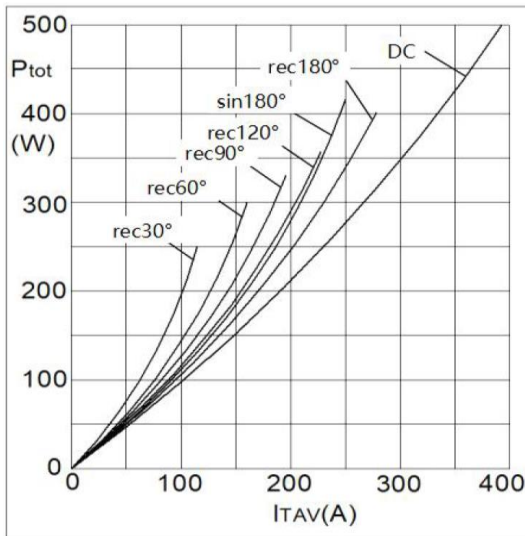
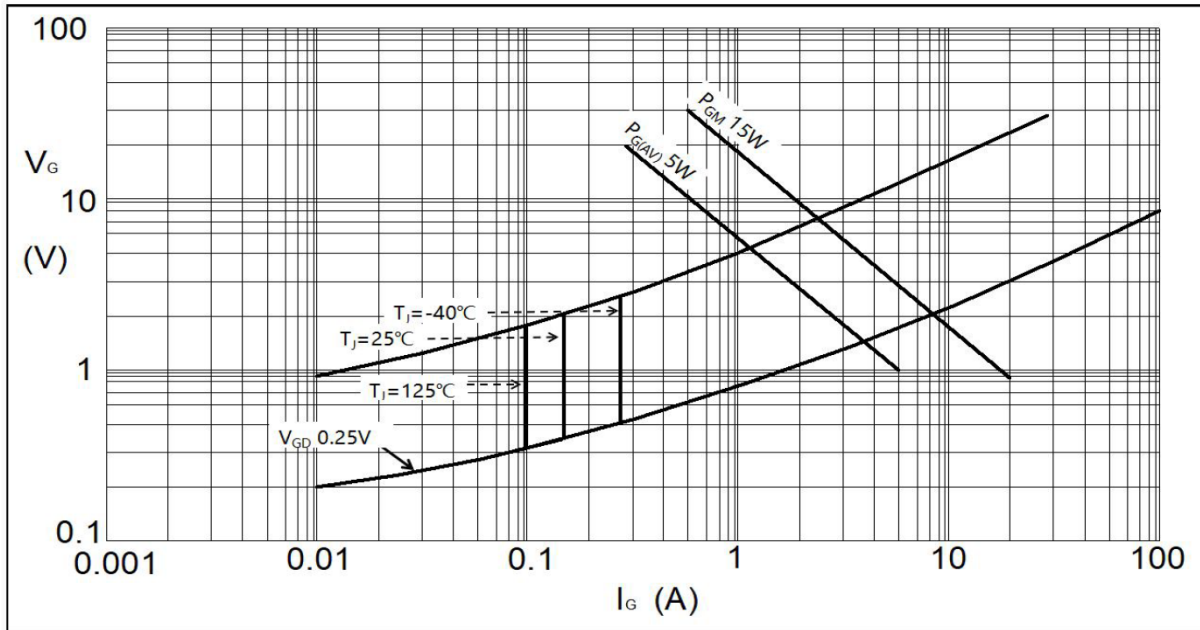
- International standard package
- High surge capability
- Glass passivated chip
- Aluminum oxide DBC
- UL recognized, file no. E312789

Typical applications:

- Power converters
- Lighting control
- AC/DC motor control and drives
- Heat and temperature control



Symbol	Characteristics	Test Conditions	Value			Unit
			Min	Typ	Max	
$V_{RSM/DSM}$	Non-repetitive reverse/forward blocking voltage	$T_j = 25^{\circ}\text{C}$			1700	V
$V_{RRM/DRM}$	Repetitive reverse/forward blocking voltage	$T_j = 25^{\circ}\text{C}$			1600	V
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz			250	A
$I_{T(RMS)}$	RMS on-state current	$T_c = 83^{\circ}\text{C}$			390	A
I_{RRM} I_{DRM}	Repetitive peak current	at V_{DRM}/V_{RRM} $T_j = 125^{\circ}\text{C}$			50	mA
I_{TSM}	Surge non repetitive current	10ms half sine wave $T_j = 25^{\circ}\text{C}$, $V_R = 0$			7000	A
$I^2 t$	$I^2 t$ for fusing coordination	10ms half sine wave, $T_j = 45^{\circ}\text{C}$			245000	A^2s
V_{TO}	Threshold voltage	$T_j = 125^{\circ}\text{C}$			0.86	V
r_T	On-state slope resistance	$T_j = 125^{\circ}\text{C}$			1.05	m Ω
V_{TM}	Peak on-state voltage	$T_j = 25^{\circ}\text{C}$; $I_T = 750\text{A}$			1.80	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM}$, $T_j = 125^{\circ}\text{C}$, linear voltage rise			1000	V/ μs
di/dt	Critical rate of rise of off-state current	$T_j = 125^{\circ}\text{C}$, $V_D = 1/2 V_{DRM}$, $I_G = 150\text{mA}$, $di_G/dt = 0.1\text{A}/\mu\text{s}$			150	A/ μs
I_{GT}	Gate trigger current	$V_D = 6\text{V}$, $T_j = 25^{\circ}\text{C}$			150	mA
V_{GT}	Gate trigger voltage				3	V
I_L	Latching current			200		mA
I_H	Holding current			150		mA
V_{GD}	Non-trigger gate voltage	$V_{DM} = 67\% V_{DRM}$, $T_j = 125^{\circ}\text{C}$			0.25	V
t_{gt}	Turn on time	$T_j = 25^{\circ}\text{C}$		3		μs
$R_{th(j-c)}$	Thermal resistance junction to case	Single side cooled per chip			0.10	$^{\circ}\text{C}/\text{W}$
$R_{th(c-s)}$	Thermal resistance case to sink	Single side cooled per chip			0.05	$^{\circ}\text{C}/\text{W}$
V_{ISO}	Isolation voltage	50Hz, RMS, $t = 1\text{min}$, $I_{ISO} : 1\text{mA (MAX)}$		3000		V
F_M	Mounting torque - copper plate (M6)		4		6	N·m
	Mounting torque - terminal (M6)		4		6	N·m
T_{stg}	Storage Temperature		-40		125	$^{\circ}\text{C}$
T_j	Operating Temperature		-40		125	$^{\circ}\text{C}$
W_t	Weight			180		g
Outline	M42G					



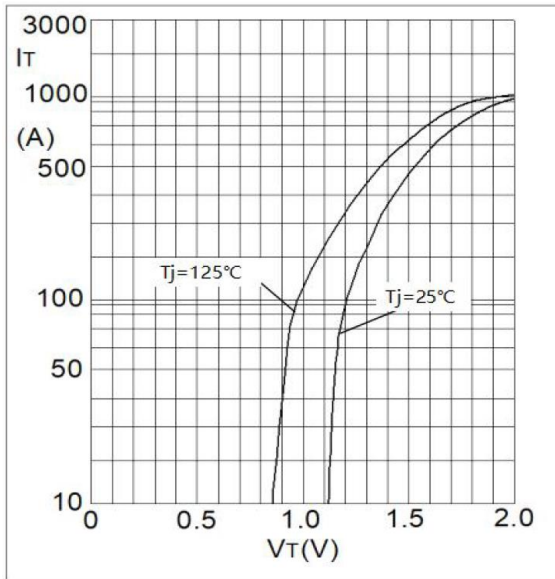


Fig4. Forward Characteristics

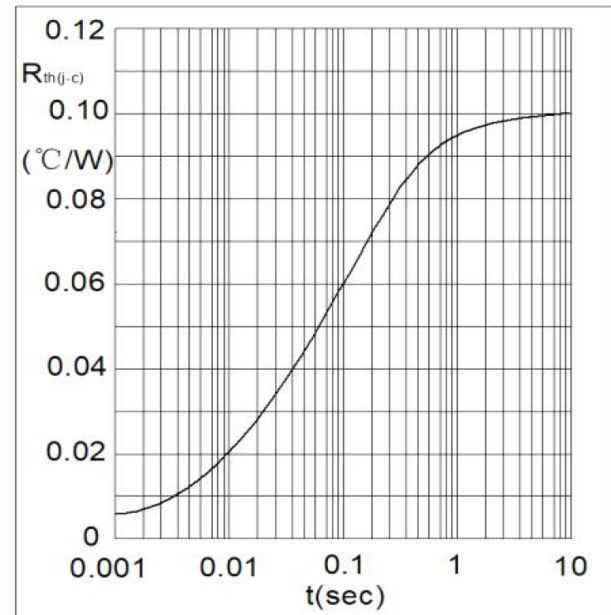


Fig5. Transient Thermal impedance

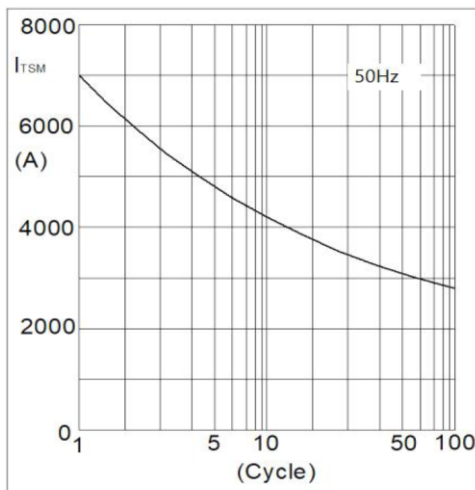
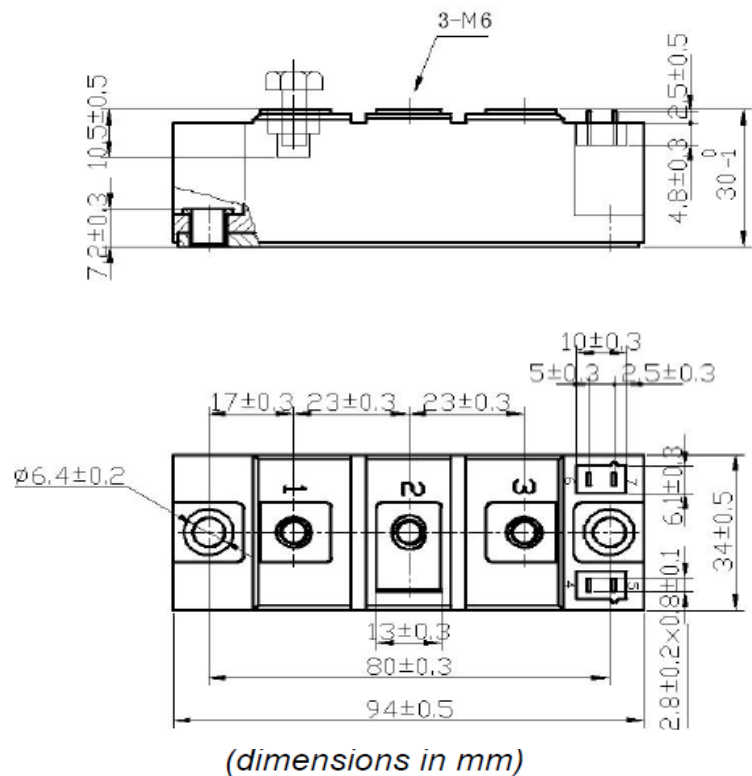


Fig6. Max Non-Repetitive Forward Surge Current



S.CO.M.E.S. Srl

Via Enrico Mattei, 6/8 - 26283 - Castiglione d'Adda (LO) - Italy

Phone: +39 0377 901243 Fax: +39 0377 900206